

FIG. 1

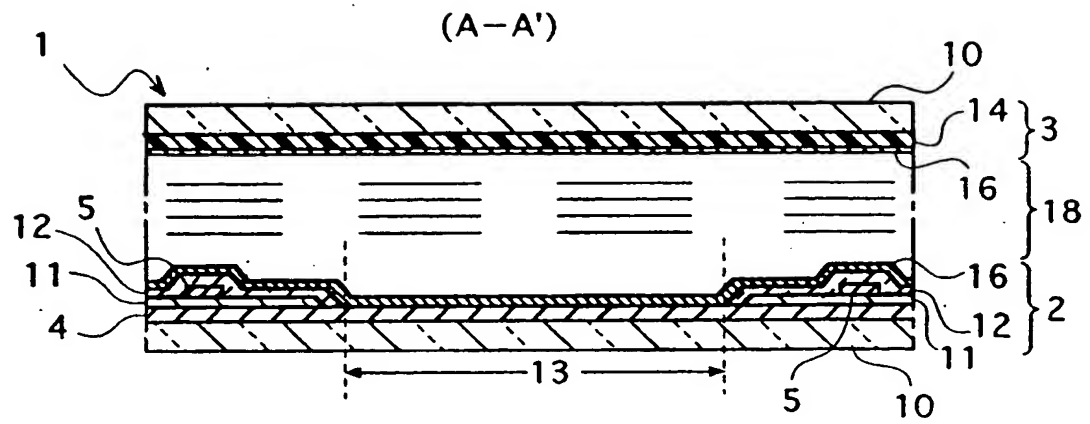


FIG. 2

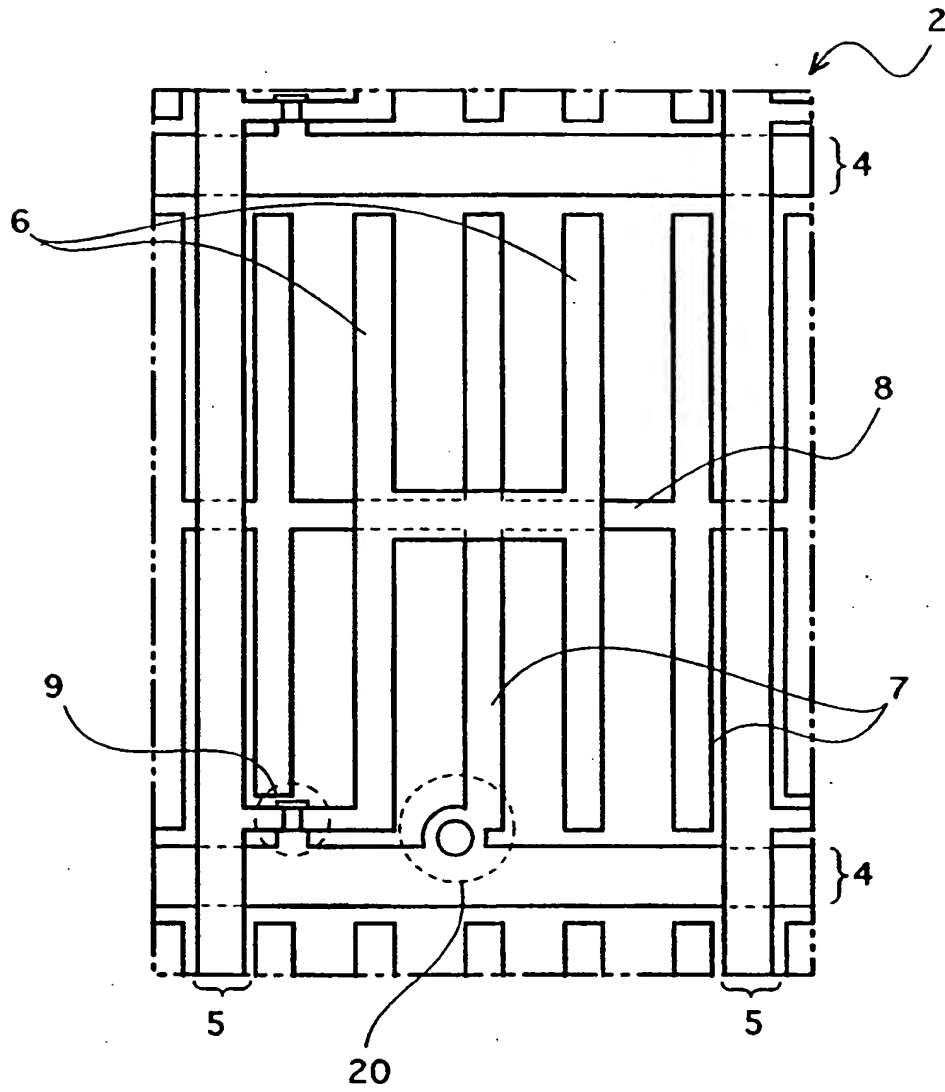


FIG. 3

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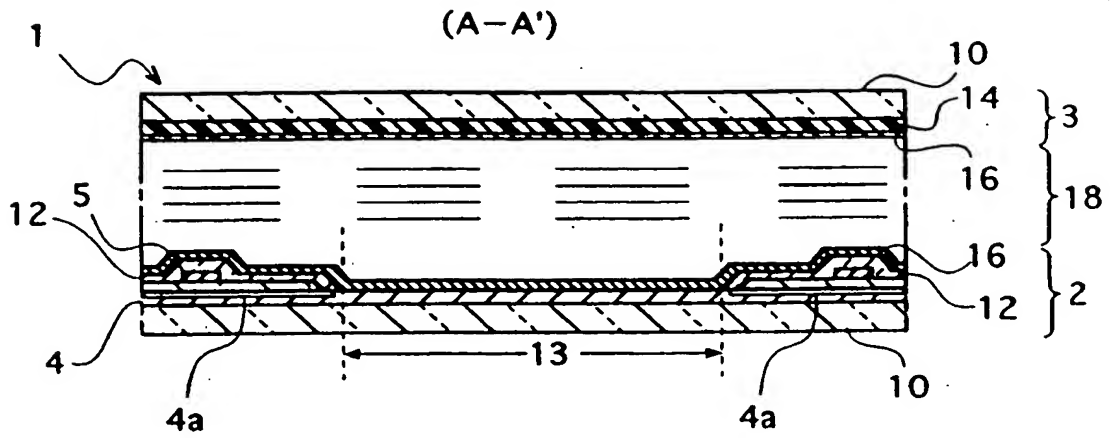


FIG. 4

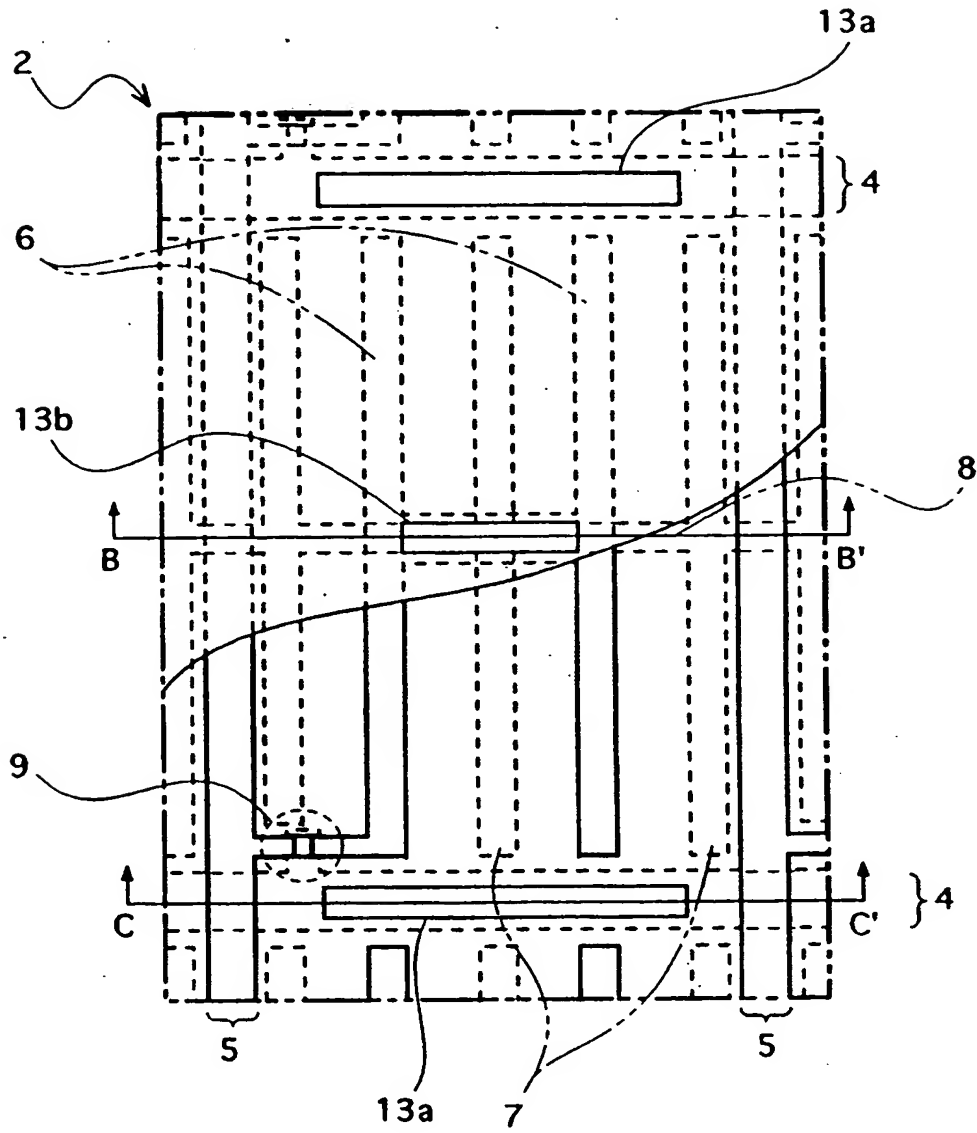


FIG. 6

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(B-B')

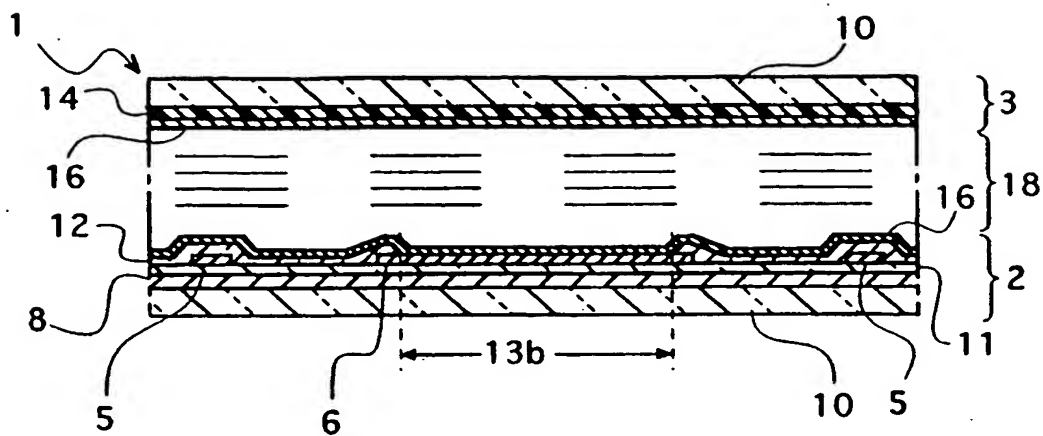


FIG. 7a

(C-C')

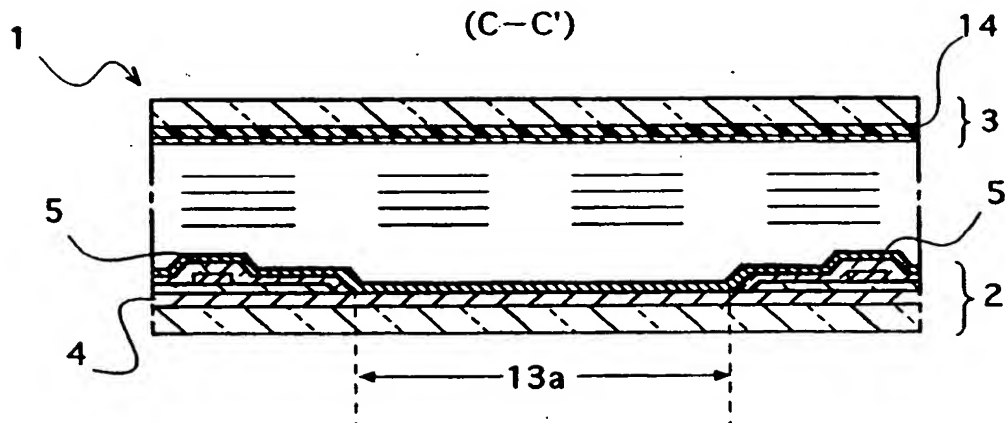


FIG. 7b

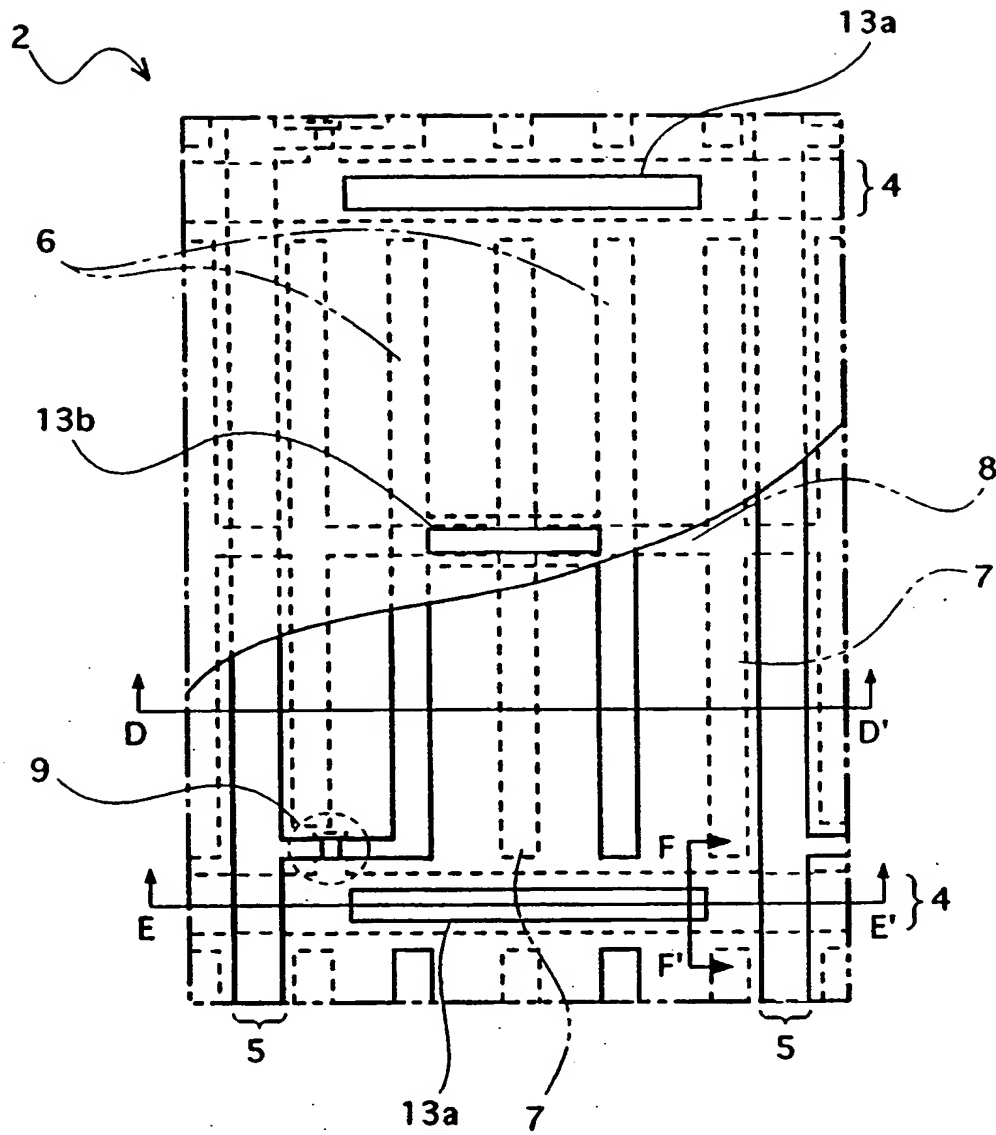


FIG. 8

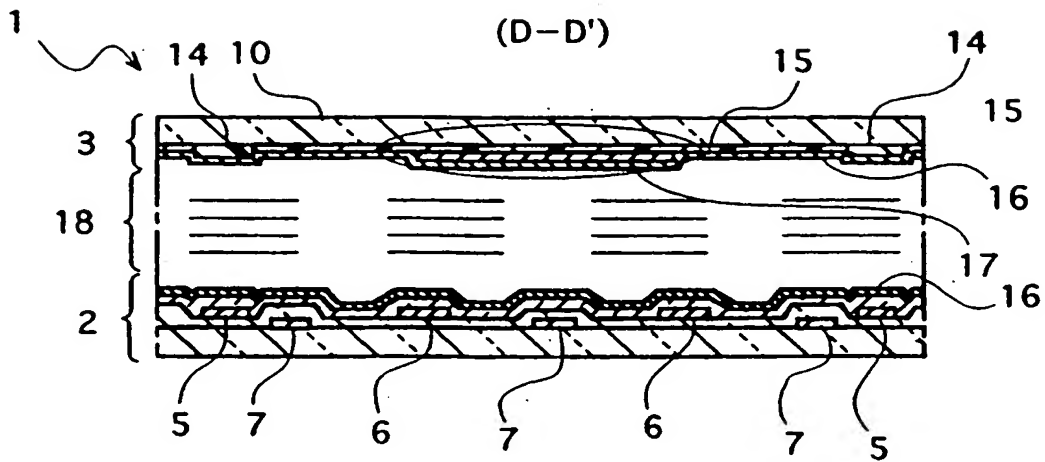


FIG. 9a

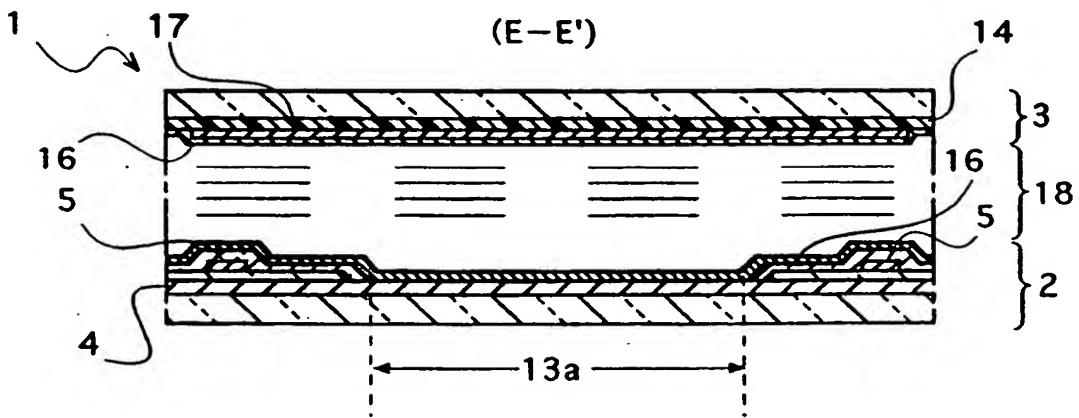


FIG. 9b

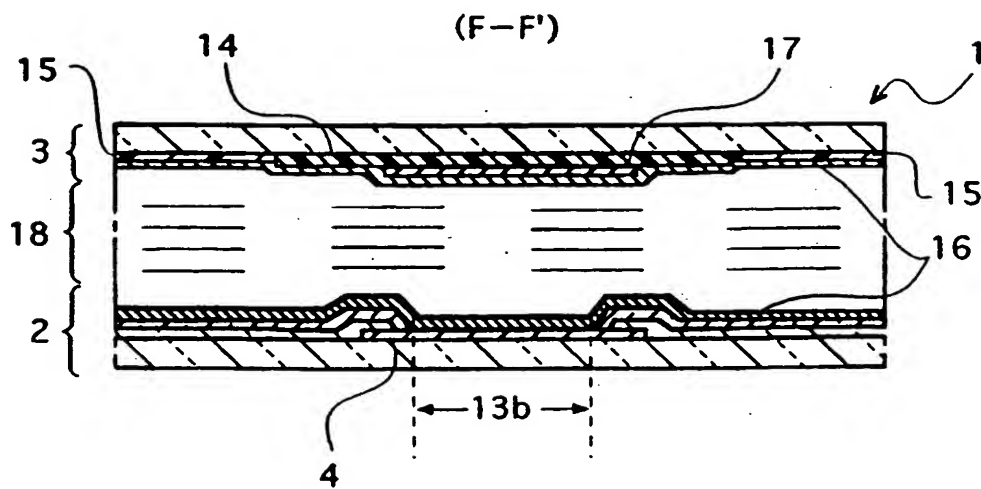


FIG. 9c

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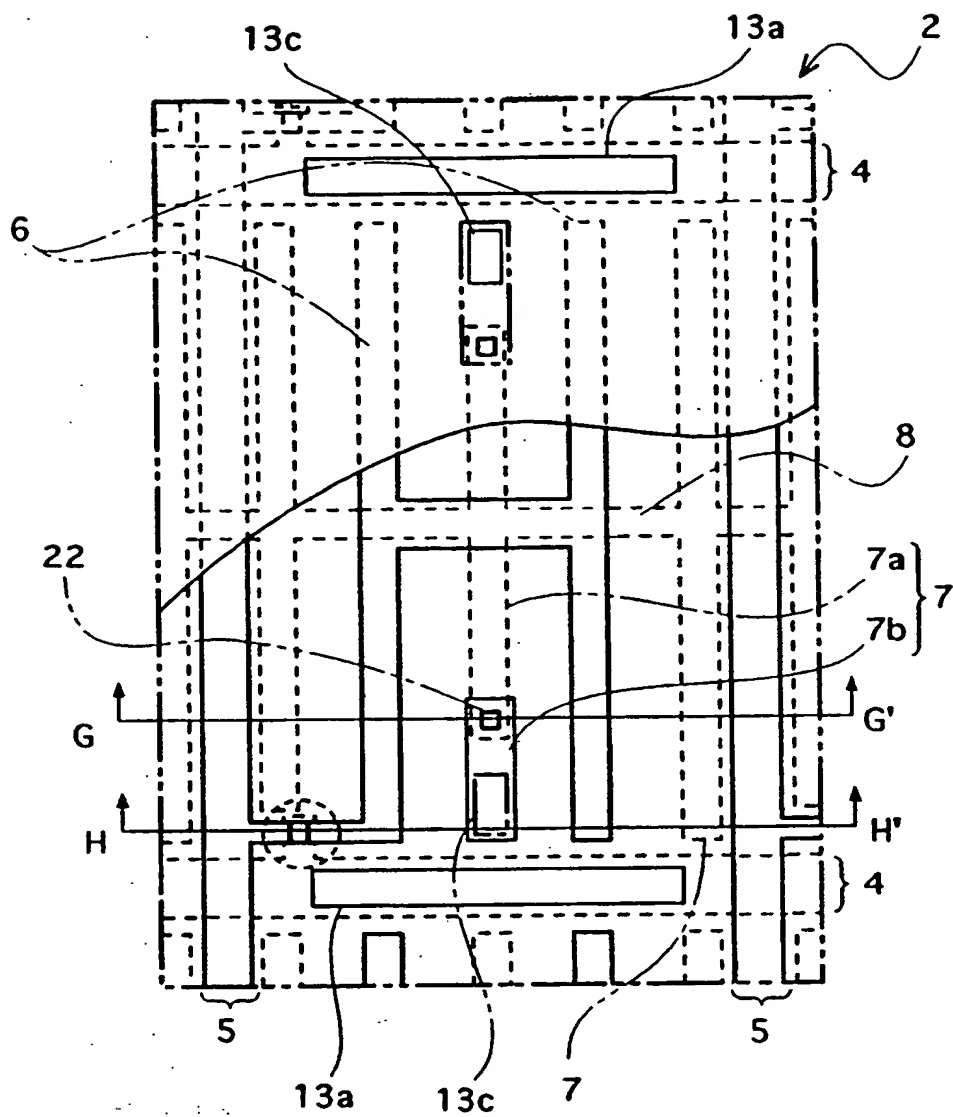


FIG.10

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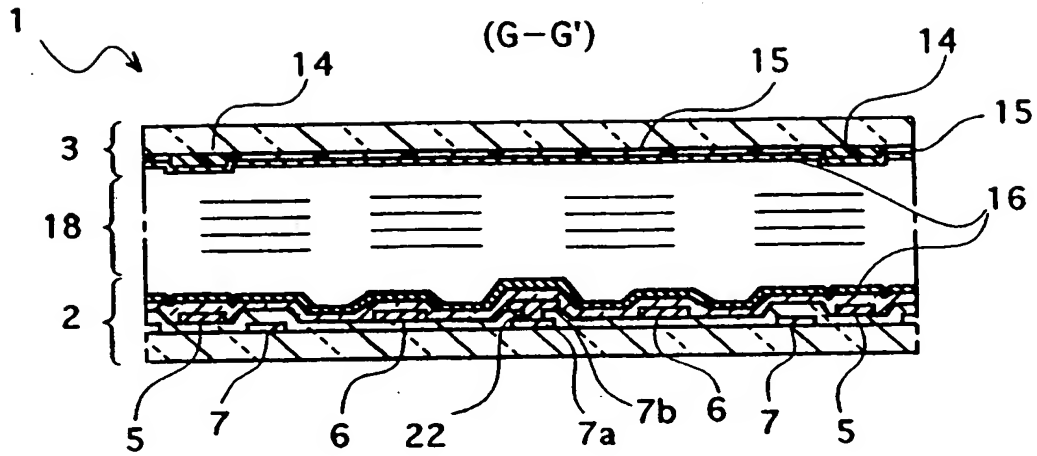


FIG.11a

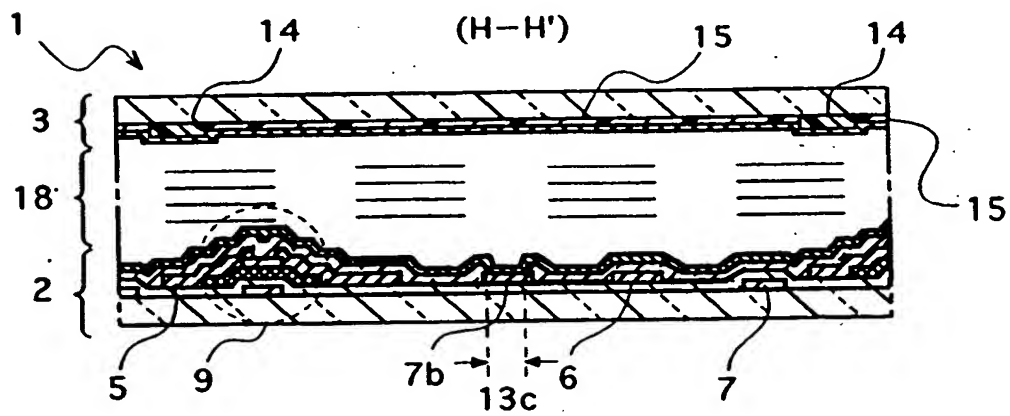


FIG.11b

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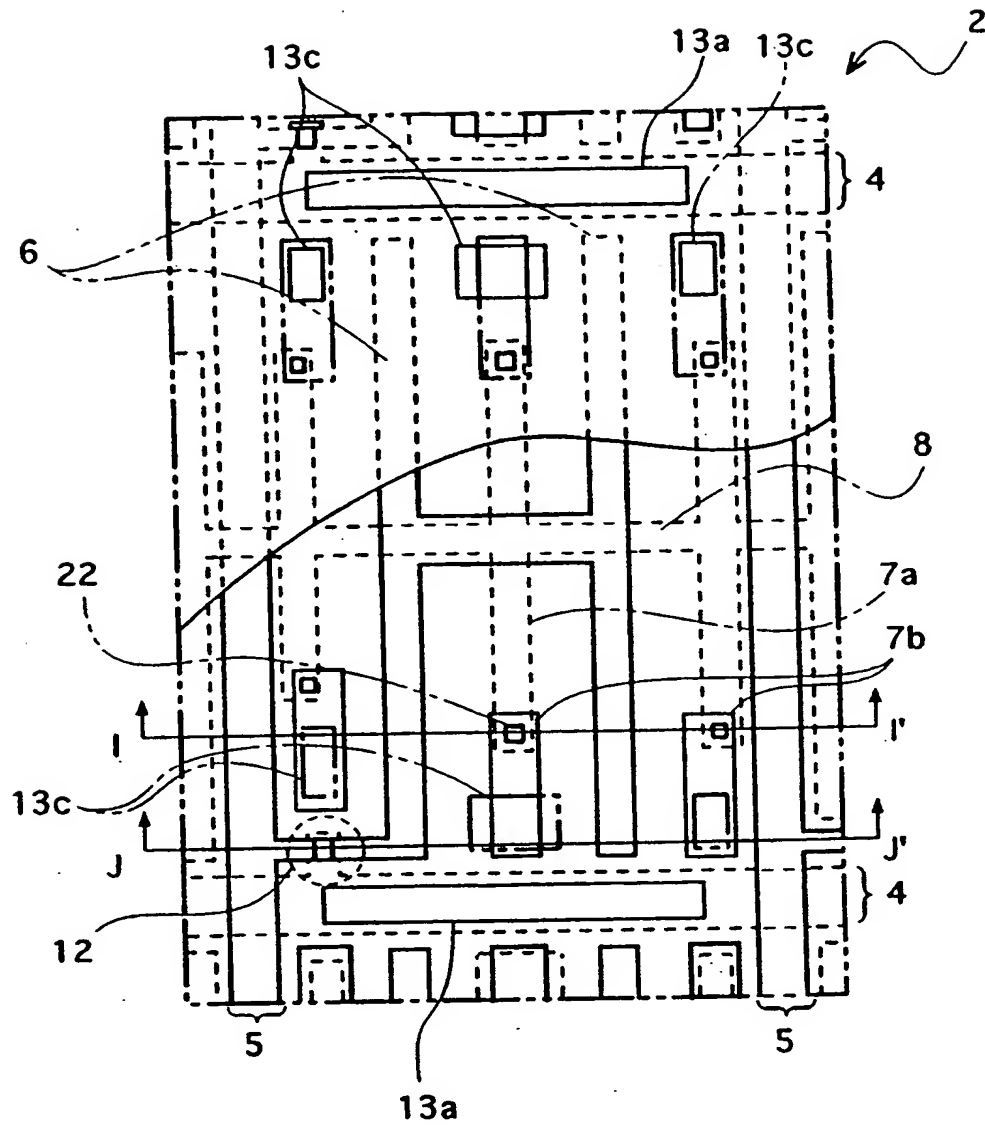


FIG. 12

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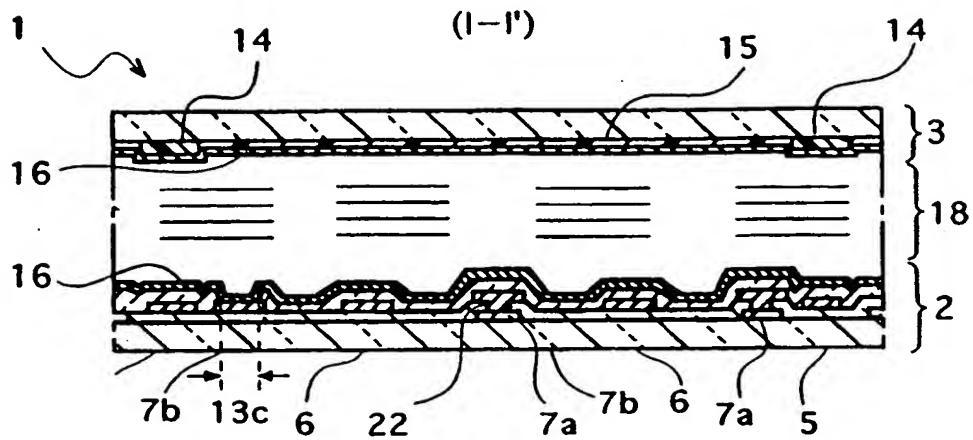


FIG. 13a

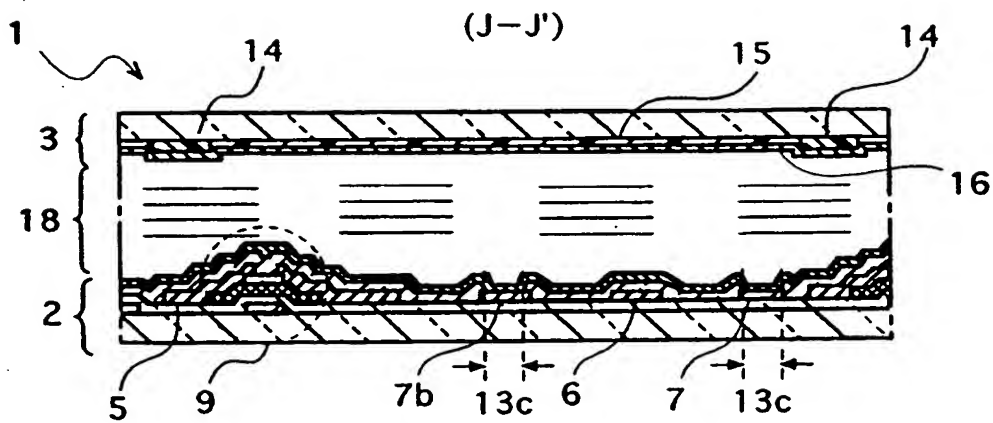


FIG. 13b

图 14



FIG. 15

A detailed cross-sectional view of a semiconductor device 1. The device consists of a substrate 8 with a top layer 5 and a bottom layer 11. A central region 12 contains a patterned layer 14. A central cavity 16 is formed within the patterned layer 14, filled with a material 21. The cavity 16 is surrounded by a layer 18. The device is further defined by a layer 6 and a layer 5. The entire structure is labeled 1.

FIG. 16b

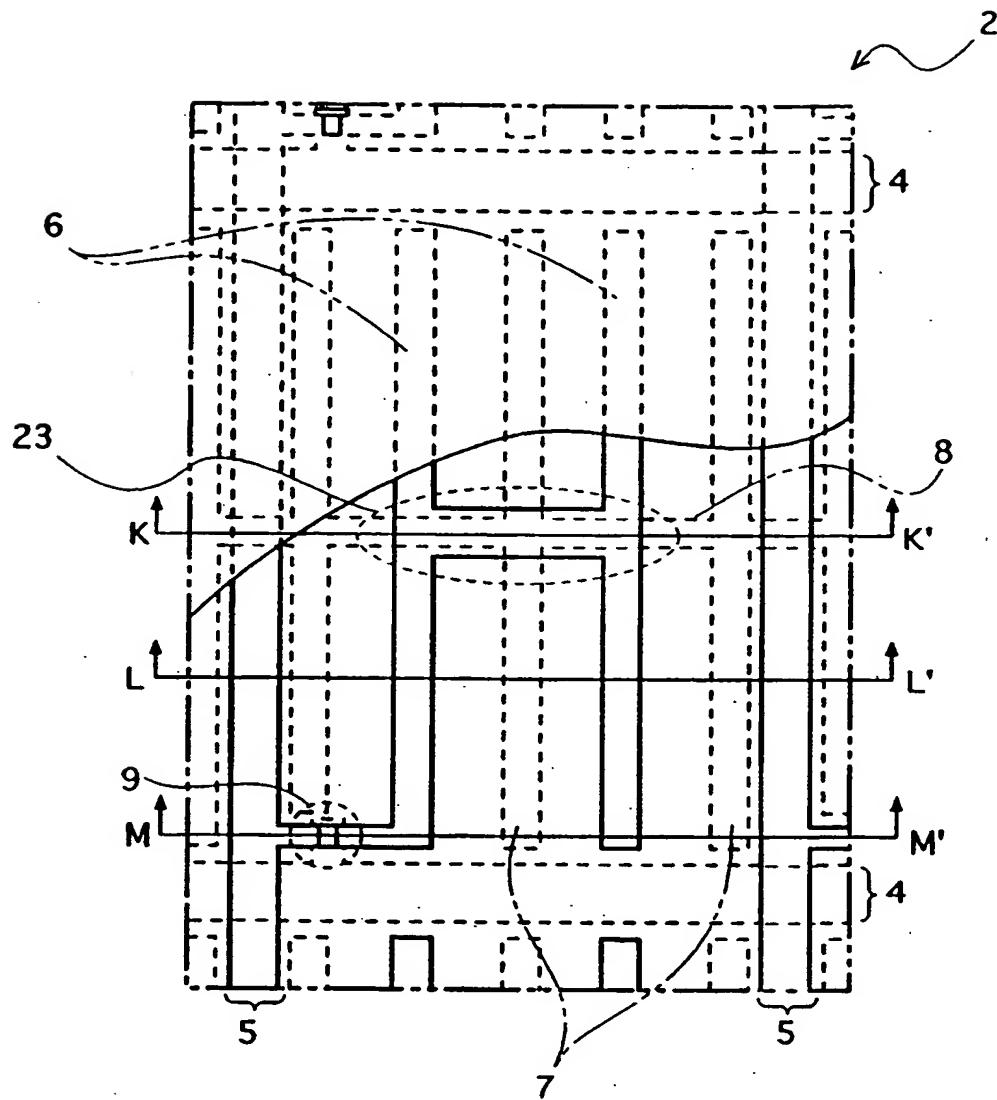


FIG. 17

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(K-K')

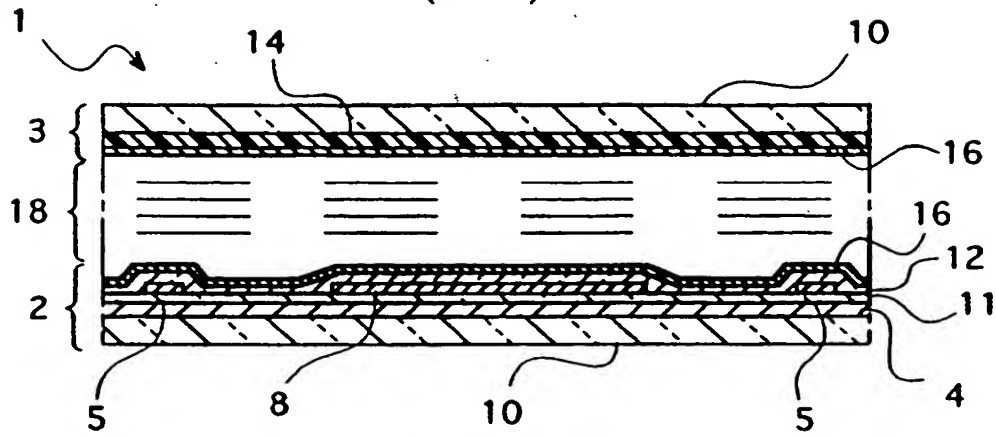


FIG.18a

(L-L')

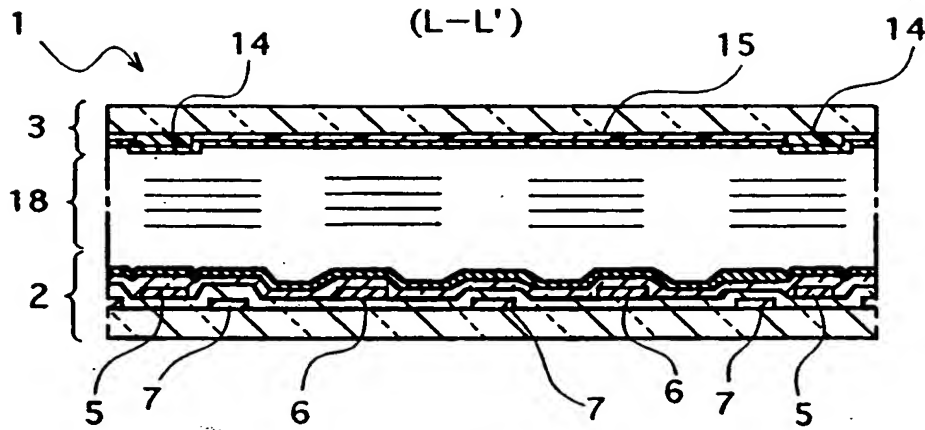


FIG.18b

(M-M')

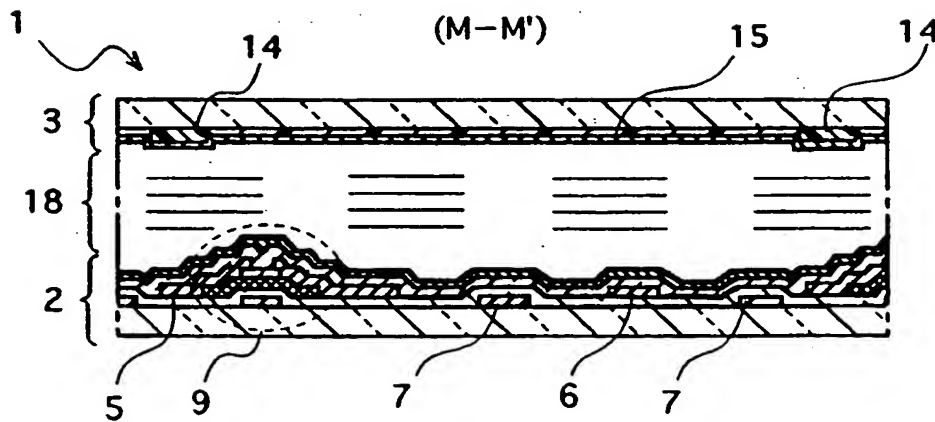


FIG.18c